

N型晶体硅电池——高效晶体硅太阳能电池

N型硅衬底的优点：N型硅（n-Si）相对于P型硅来说，由于对金属杂质和许多非金属缺陷不敏感，或者说具有很好的忍耐性能，故其少数载流子具有较长而且稳定的扩散长度。

目前只有Sunpower和sanyo两家企业N型Si衬底生产高效太阳能电池做得较好。英利“熊猫”N型单晶硅高效电池项目填补了国内N型电池技术的空白。

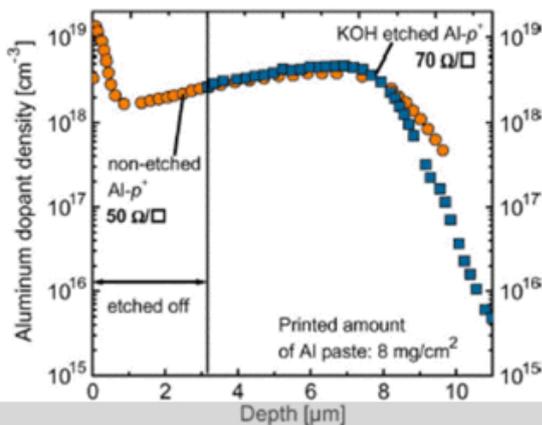
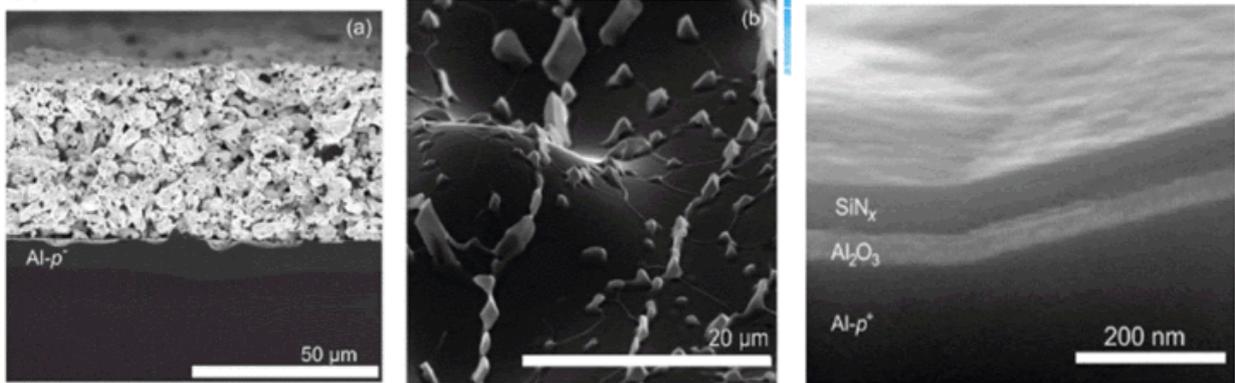
如何在N型硅衬底上实现PN结：硼扩散制结、非晶硅/晶硅异质结以及Al扩散制结三种基本方法。

硼扩散制结需要高温，高温是太阳能电池制备工艺最忌讳的！

HIT电池只有Sanyo做得较好，没有推广。

Al推进制结目前受到普遍关注，因其价格低廉而又容易实现。具体工艺参数信息见附图，对专业人士很有参考价值。（作者 和海一样的新能源 [微博](#)）

Al推进形成PN结

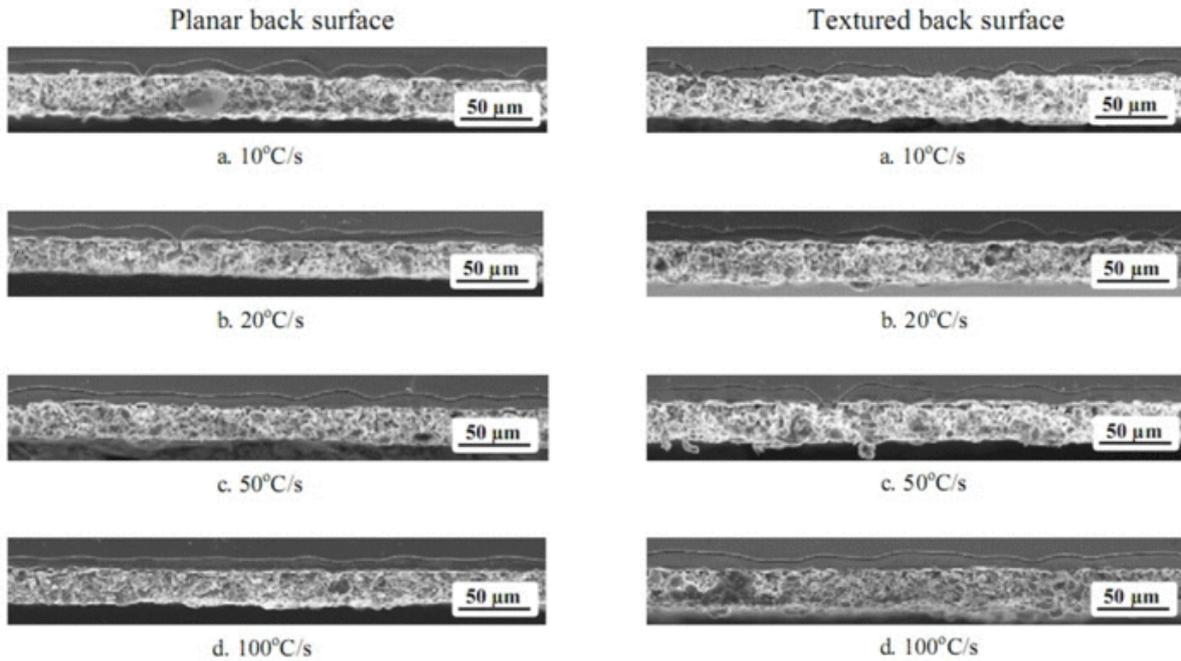


Cell ID	V_{oc} [mV]	J_{sc} [mA/cm ²]	FF [%]	η [%]
P01	649	39.1	77.5	19.7* [21]
P25	636	39.5	79.5	20.0*
P15	639	39.9	77.2	19.7*

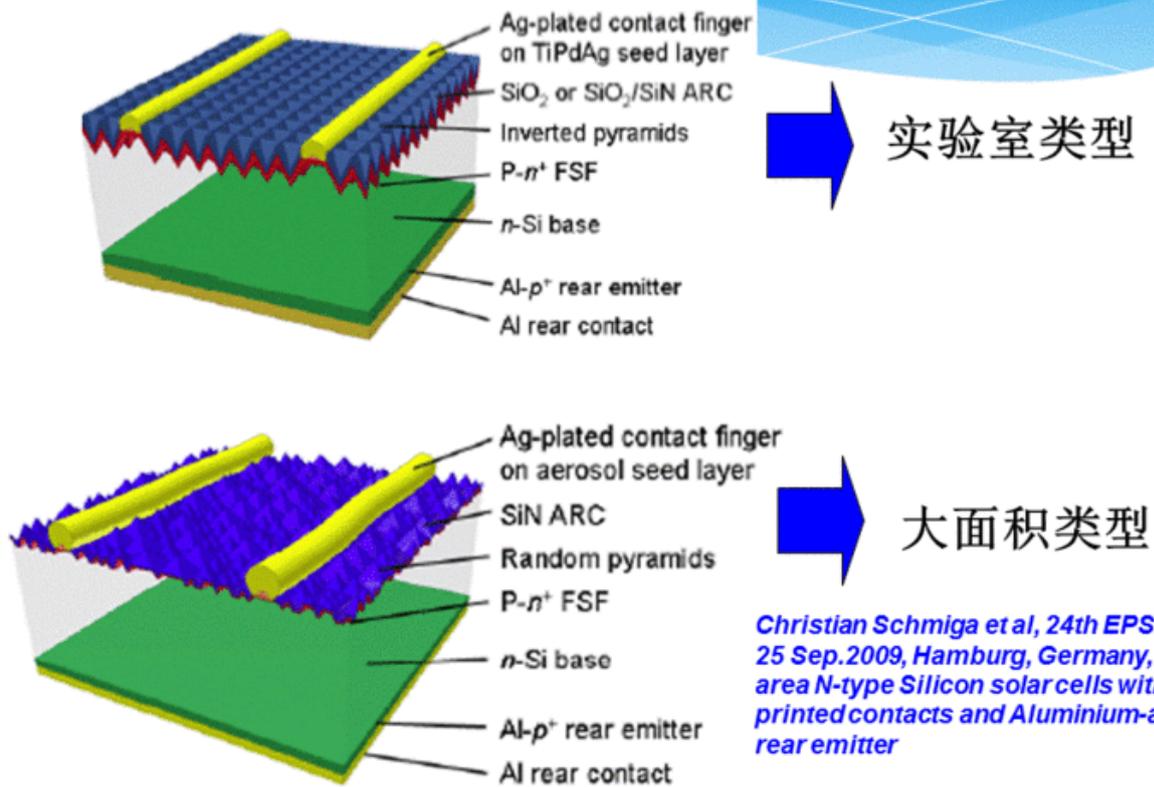
* independently confirmed at Fraunhofer ISE CalLab

R. Bock, IEEE TED, vol.57, No.8, 2010, The ALU+ Concept: N-Type Silicon Solar Cells With Surface-Passivated Screen-Printed Aluminum-Alloyed Rear Emitter

退火处理及方式对开路电压等有着重要影响

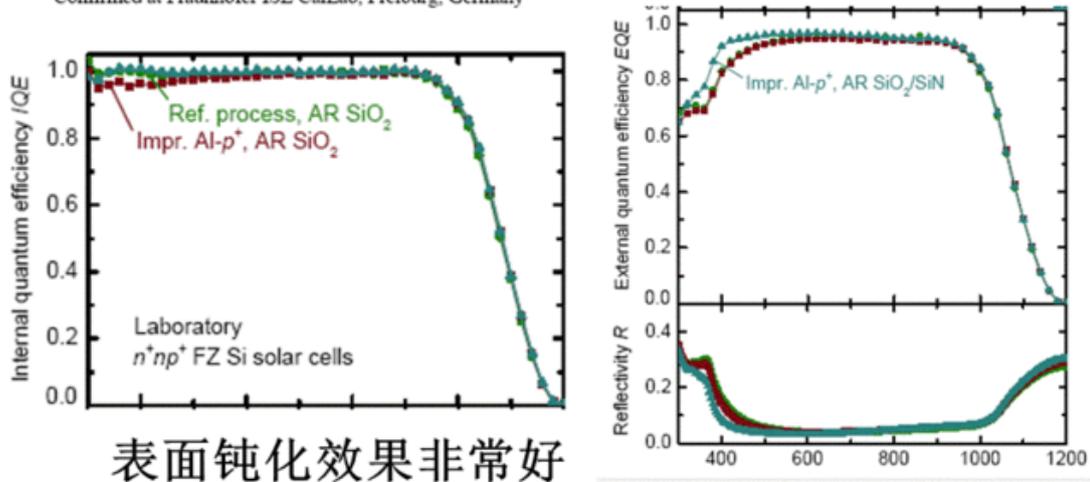


AI推进形成背发射极PN结



Cell type	Cell area [cm ²]	Front contact grid	Further details	V _{oc} [mV]	J _{sc} [mA/cm ²]	FF [%]	η [%]
Laboratory	4.0 (aperture)	Evaporated TiPdAg seed layer, Ag-plated	Reference process [2], AR SiO ₂	625	38.4	79.1	19.0*
			Improved rear Al-p ⁺ , AR SiO ₂	640	37.9	79.4	19.2*
			Improved rear Al-p ⁺ , AR 10 nm SiO ₂ /SiN	642	38.7	79.6	19.8*
Industrial	148.5 (total)	Aerosol-printed seed layer, Ag-plated	AR SiN	632	36.0	80.0	18.2*

* Confirmed at Fraunhofer ISE CalLab, Freiburg, Germany



表面钝化效果非常好

原文地址：<http://www.china-nengyuan.com/news/37443.html>